GaAs MMIC Low Noise Amplifier for Micro Wave Application

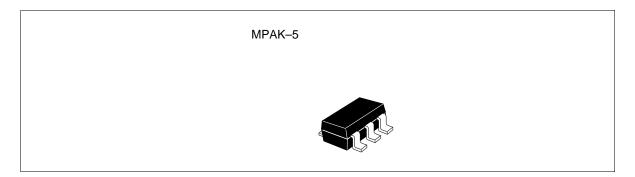
HITACHI

ADE-207-266 (Z) 1st. Edition October 1998

Features

- Suitable for low noise amplifier of Micro Wave Application(1.5 to 1.9GHz)
- Low voltage and low current operation (2.7V, 1.7mA typ.)
- Low noise (1.4 dB typ. @1.5GHz)
- High power gain (14 dB typ. @1.5GHz)
- Built–in matching circuits (50Ω)
- Small surface mount package (MPAK–5)

Outline



This document may, wholly or partially, be subject to change without notice.

This Device si sensitive to Electro Static Discharge.

An Adequate handling procedure is requested.

CAUTION

This product ues GaAs. Since dust or fume of GaAs is highly poisonous to human body, please do not treat them mechanically in the manner which might expose to the Aer. And it should never be thrown

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit	
Supply voltage	Vdd	5	V	
Maximum current	Idd	6	mA	
Power dissipation	Pd	100	mW	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +125	°C	
Operation temperature	Topr	-20 to +70	°C	
Maximum input power	Pin max	+15	dBm	

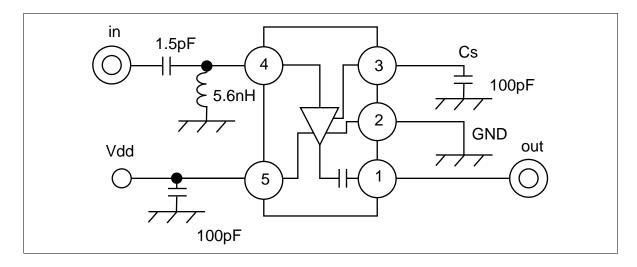
Electrical Characteristics (Ta = 25°C, Vdd = 2.7V)

Item	Symbol	Min	Тур	Мах	Unit	Test Conditions	Pin
Quiescent current	ldd	—	1.7	2.5	mA	No signal	
Power gain	PG	12	14		dB	f = 1.5 GHz	
Noise figure	NF		1.4	2	dB	f = 1.5 GHz	

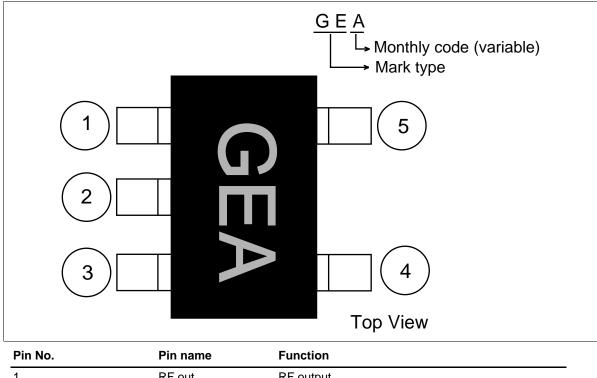
Typical Performance (Ta = 25° C, Vdd = 2.7V)

Item	Symbol	Тур	Unit	Test Conditions	Pin
VSWR (input)	VSWR in	1.5	_	f = 1.5 GHz	4
VSWR (output)	VSWR out	2.2	_	f = 1.5 GHz	1
3rd order intermodulation distortion	IM3	50	dB	f = 1.5 GHz, Pin = -30 dBm	

Block Diagram

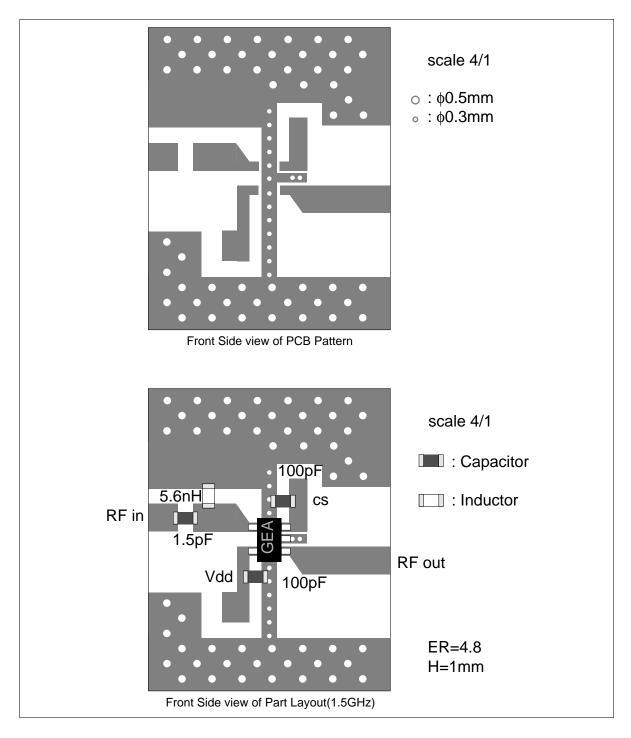


Pin Arrangement

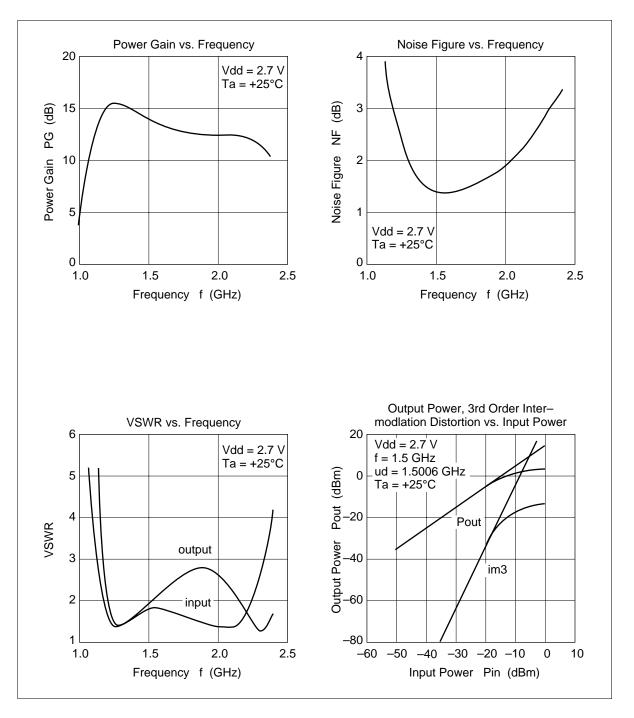


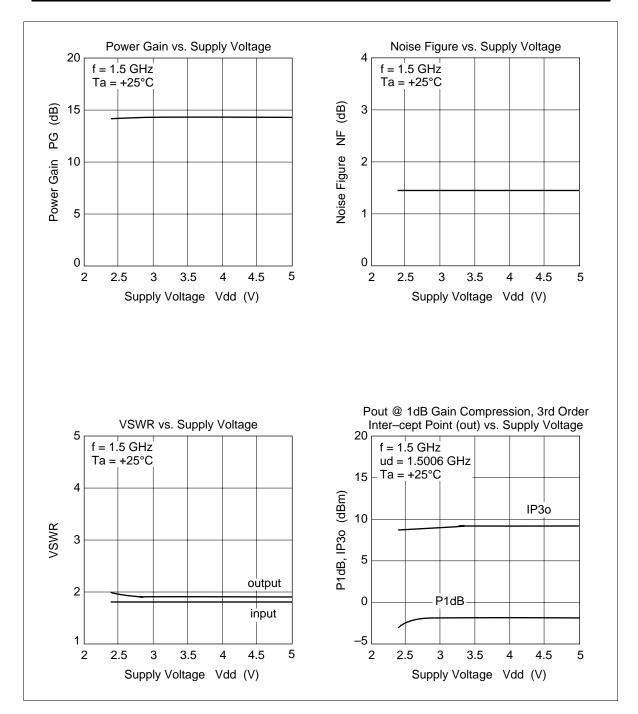
1	RF out	RF output
2	GND	Ground
3	Cs	Bypath capacitor (>100 pF)
4	RF in	RF input
5	Vdd	Power supply

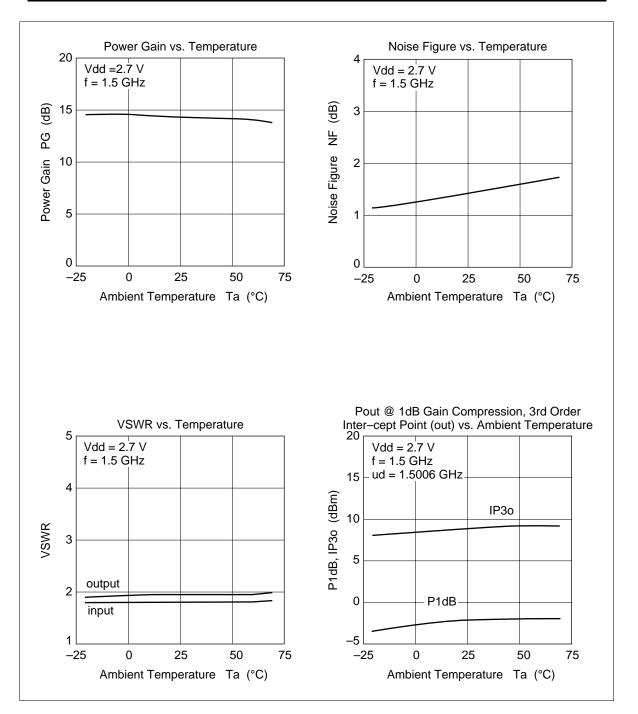
Pattern Layout

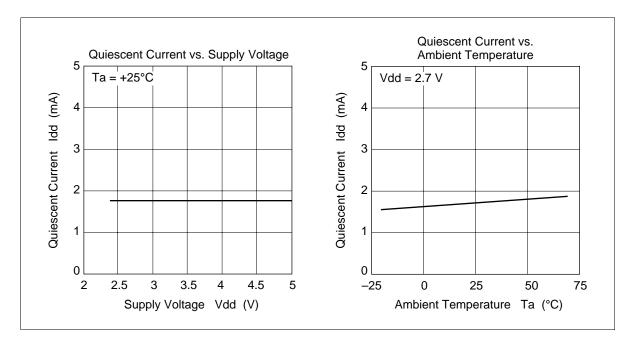


Main Characteristics



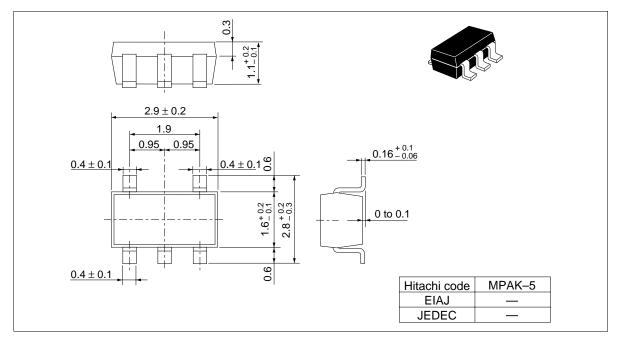






Package Dimentions

Unit: mm



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